

# FDB86102LZ

## N-Channel PowerTrench® MOSFET 100 V, 30 A, 24 mΩ

### Features

- Max  $r_{DS(on)}$  = 24 mΩ at  $V_{GS} = 10$  V,  $I_D = 8.3$  A
- Max  $r_{DS(on)}$  = 35 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 6.8$  A
- HBM ESD protection level > 6 kV typical (Note 4)
- Very low  $Q_g$  and  $Q_{gd}$  compared to competing trench technologies
- Fast switching speed
- 100% UIL Tested
- RoHS Compliant

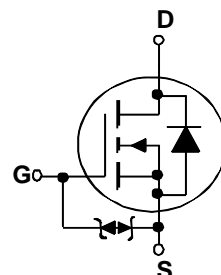
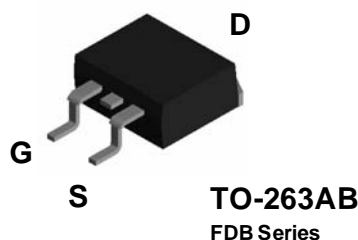


### General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance and switching loss. G-S zener has been added to enhance ESD voltage level.

### Applications

- DC-DC conversion
- Inverter
- Synchronous Rectifier



### MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	100	V
$V_{GS}$	Gate to Source Voltage	±20	V
$I_D$	Drain Current -Continuous(Package limited) $T_C = 25$ °C	30	A
	-Continuous (Silicon limited) $T_C = 25$ °C	40	
	-Continuous $T_A = 25$ °C (Note 1a)	8.3	
	-Pulsed	50	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	121	mJ
$P_D$	Power Dissipation $T_A = 25$ °C (Note 1a)	3.1	W
	Power Dissipation $T_A = 25$ °C (Note 1b)	2	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	1.9	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	40	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB86102LZ	FDB86102LZ	TO-263AB	330mm	24 mm	800 units

**Electrical Characteristics**  $T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$		69		mV/ $^{\circ}\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$			$\pm 10$	$\mu\text{A}$

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$	1.0	1.5	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$		-6		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 8.3\text{ A}$		18	24	m $\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 6.8\text{ A}$		23	35	
		$V_{GS} = 10\text{ V}$ , $I_D = 8.3\text{ A}$ , $T_J = 125\text{ }^{\circ}\text{C}$		31	42	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}$ , $I_D = 8.3\text{ A}$		29		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 50\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$		959	1275	pF
$C_{oss}$	Output Capacitance			181	240	pF
$C_{rss}$	Reverse Transfer Capacitance			9	13	pF
$R_g$	Gate Resistance			0.4		$\Omega$

**Switching Characteristics**

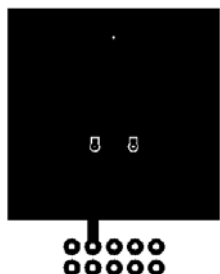
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{ V}$ , $I_D = 8.3\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		6.6	13	ns
$t_r$	Rise Time			2.1	10	ns
$t_{d(off)}$	Turn-Off Delay Time			18.2	33	ns
$t_f$	Fall Time			2.3	10	ns
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to $10\text{ V}$	$V_{DD} = 50\text{ V}$ , $I_D = 8.3\text{ A}$	15.2	21	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to $4.5\text{ V}$		7.6	11	nC
$Q_{gs}$	Gate to Source Charge			2.4		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			2.5		nC

**Drain-Source Diode Characteristics**

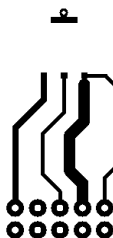
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 8.3\text{ A}$ (Note 2)		0.8	1.3	V
		$V_{GS} = 0\text{ V}$ , $I_S = 2.4\text{ A}$ (Note 2)		0.7	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 8.3\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		42	67	ns
$Q_{rr}$	Reverse Recovery Charge			40	64	nC

## NOTES:

1.  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a) 40  $^{\circ}\text{C}/\text{W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b) 62.5  $^{\circ}\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0 %.

3. Starting  $T_J = 25\text{ }^{\circ}\text{C}$ ,  $L = 3\text{ mH}$ ,  $I_{AS} = 9\text{ A}$ ,  $V_{DD} = 100\text{ V}$ ,  $V_{GS} = 10\text{ V}$ .

4. The diode connected between gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

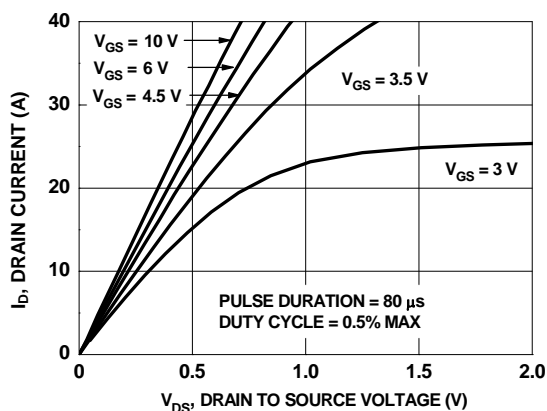


Figure 1. On Region Characteristics

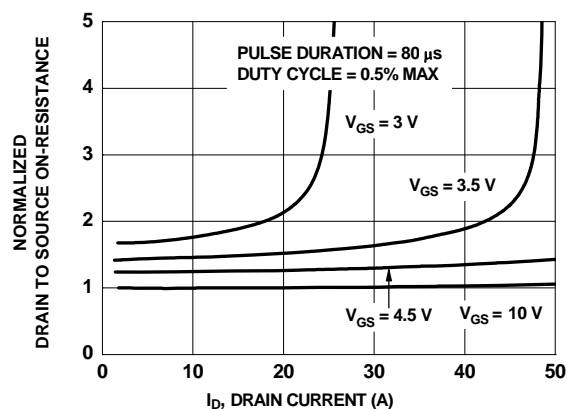


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

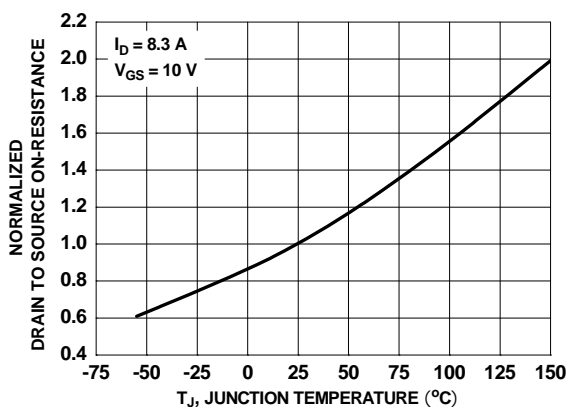


Figure 3. Normalized On Resistance vs Junction Temperature

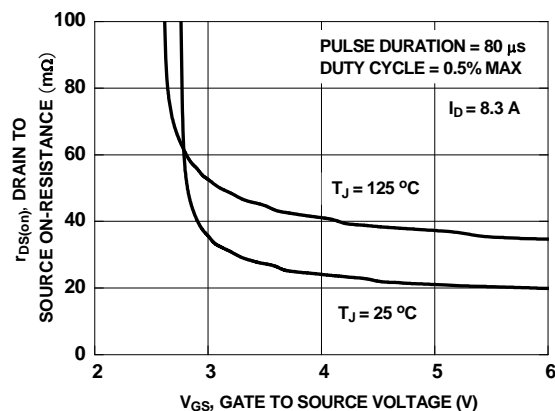


Figure 4. On-Resistance vs Gate to Source Voltage

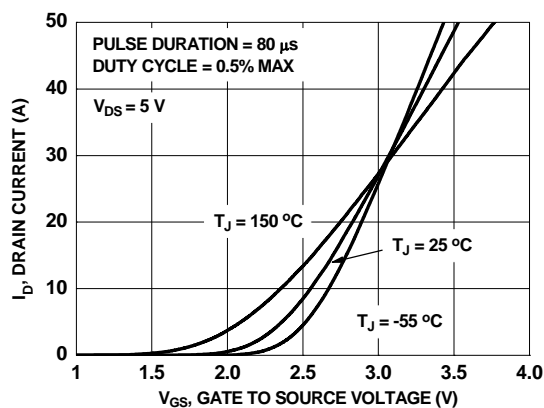


Figure 5. Transfer Characteristics

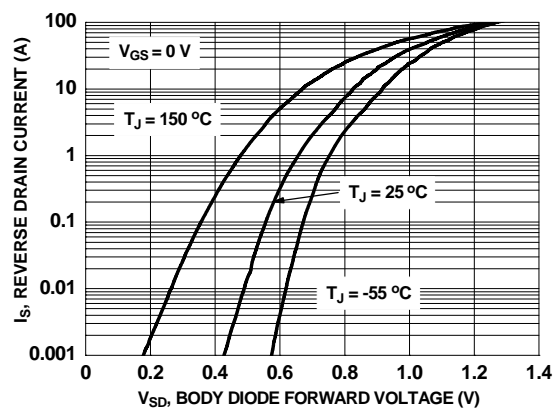


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

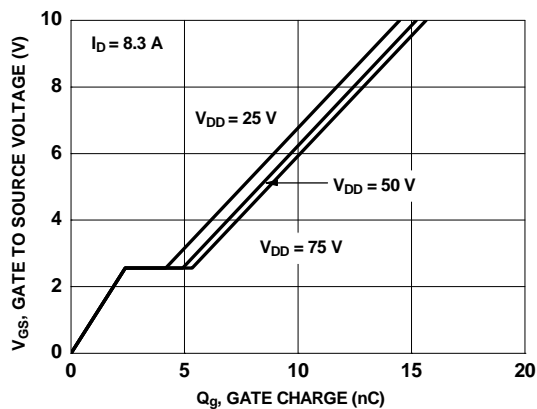


Figure 7. Gate Charge Characteristics

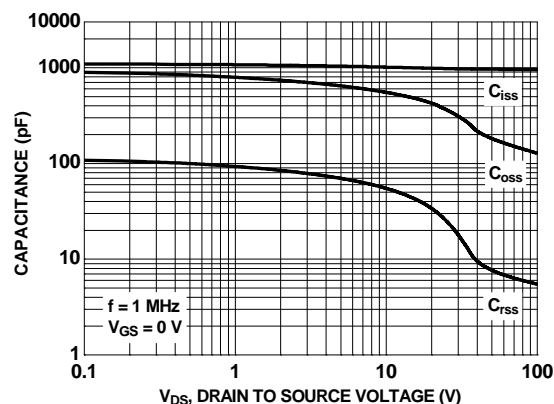


Figure 8. Capacitance vs Drain to Source Voltage

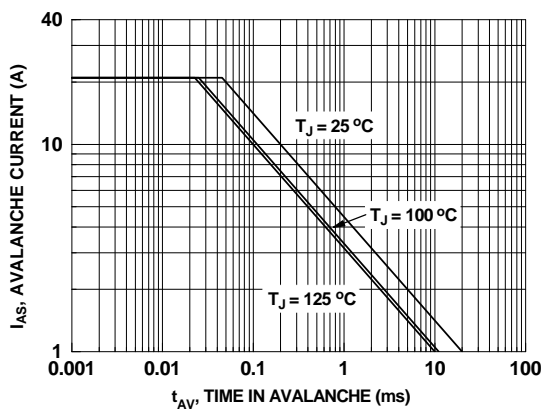


Figure 9. Unclamped Inductive Switching Capability

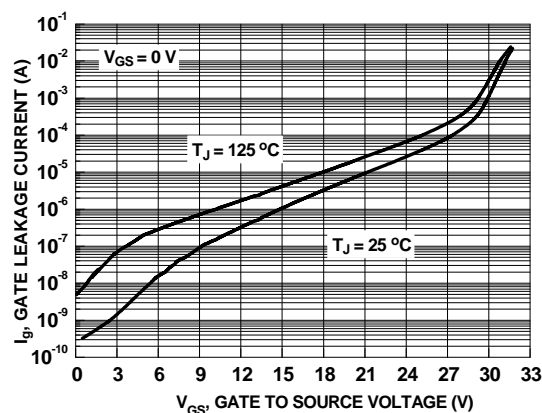


Figure 10. Gate Leakage Current vs Gate to Source Voltage

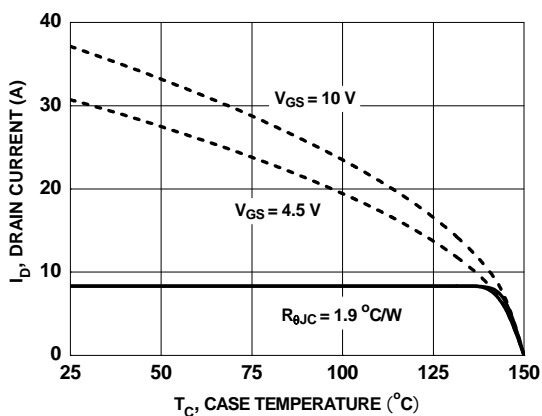


Figure 11. Maximum Continuous Drain Current vs Case Temperature

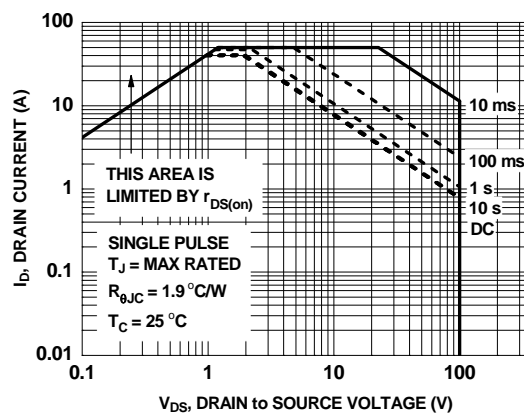


Figure 12. Forward Bias Safe Operating Area

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

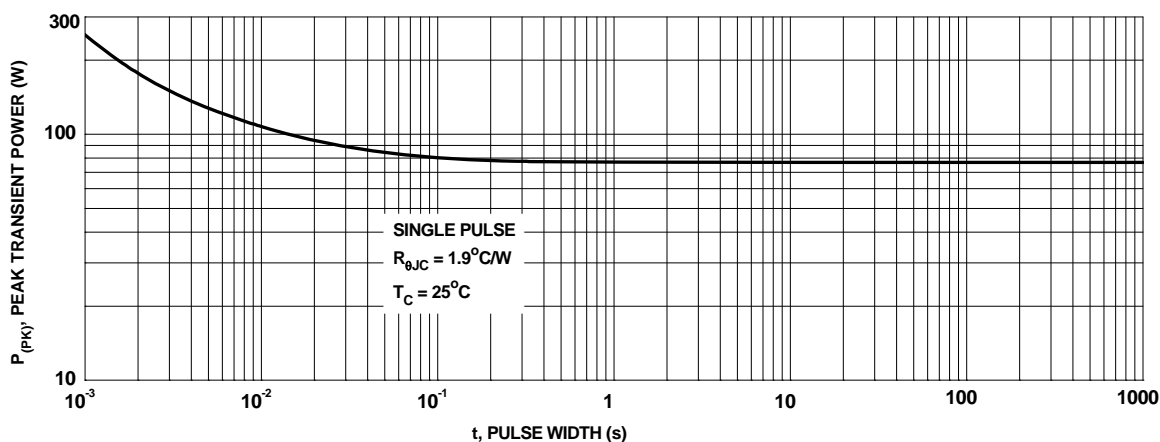


Figure 13. Single Pulse Maximum Power Dissipation

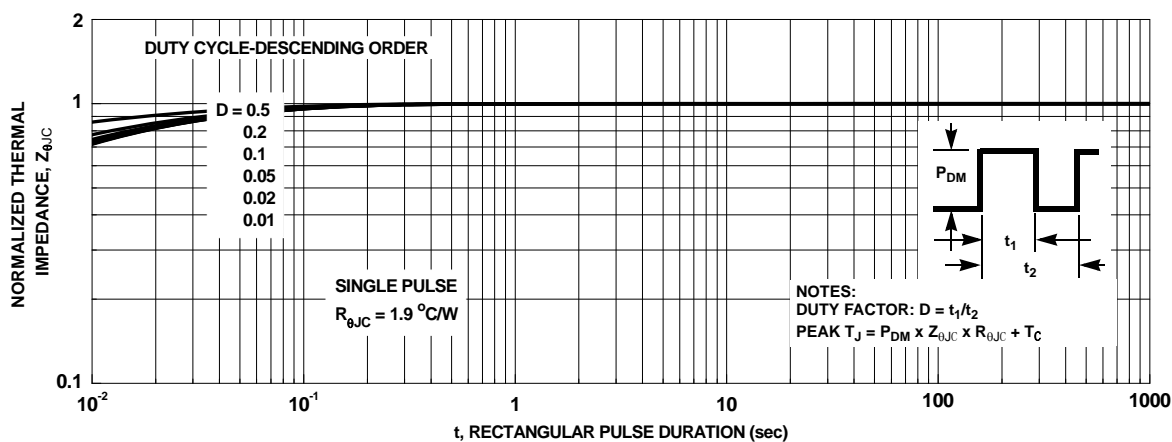





Figure 14. Junction-to-Case Transient Thermal Response Curve



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